Low-power dual inverting buffer/line driver; 3-state

Rev. 8 — 24 January 2013

Product data sheet

1. General description

The 74AUP2G240 provides the dual inverting buffer/line <u>driver</u> with 3-state output. <u>The</u> 3-state output is controlled by the output enable input (nOE). A HIGH level at pin nOE causes the output to assume a high-impedance OFF-state.

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using I_{OFF}.

The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

This device has the input-disable feature, which allows floating input signals. The inputs are disabled when the output enable input nOE is HIGH.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - ◆ HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD78 Class II
- Inputs accept voltages up to 3.6 V
- Low-noise overshoot and undershoot < 10 % of V_{CC}
- Input-disable feature allows floating input conditions
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AUP2G240DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74AUP2G240GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 \times 1.95 \times 0.5 mm	SOT833-1
74AUP2G240GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 \times 1 \times 0.5 mm	SOT1089
74AUP2G240GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body $3\times2\times0.5~\text{mm}$	SOT996-2
74AUP2G240GM	–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 \times 1.6 \times 0.5 mm	SOT902-2
74AUP2G240GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.2 \times 1.0 \times 0.35 mm	SOT1116
74AUP2G240GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1.0 \times 0.35$ mm	SOT1203

4. Marking

Table 2. Marking codes

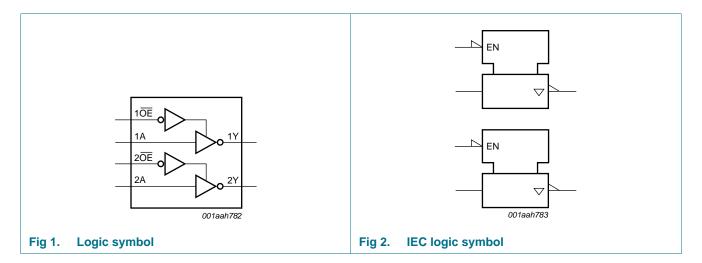
Type number	Marking code ^[1]
74AUP2G240DC	p40
74AUP2G240GT	p40
74AUP2G240GF	p2
74AUP2G240GD	p40
74AUP2G240GM	p40
74AUP2G240GN	p2
74AUP2G240GS	p2

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

NXP Semiconductors 74AUP2G240

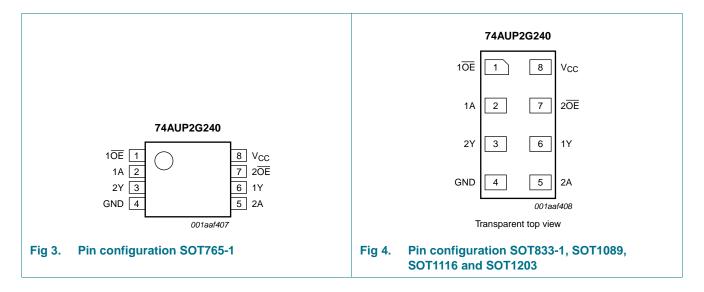
Low-power dual inverting buffer/line driver; 3-state

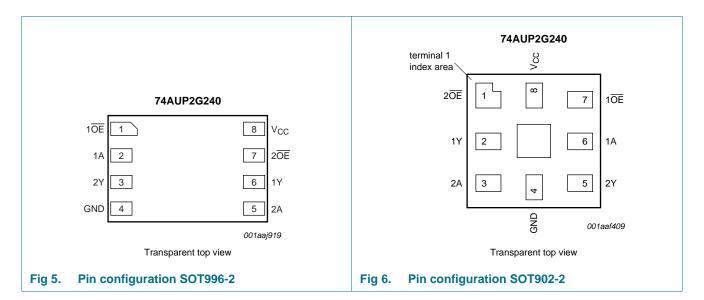
5. Functional diagram



6. Pinning information

6.1 Pinning





6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2	
1 0E , 2 0E	1, 7	7, 1	output enable input (active LOW)
1A, 2A	2, 5	6, 3	data input
GND	4	4	ground (0 V)
1Y, 2Y	6, 3	2, 5	data output
V _{CC}	8	8	supply voltage

7. Functional description

Table 4. Function table[1]

Input nOE		Output
nOE	nA	nY
L	L	Н
L	Н	L
Н	X	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
I _O	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±20	mA
I _{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T_{amb} = -40 °C to +125 °C	[2] _	250	mW

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		0.8	3.6	V
V_{I}	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V_{CC}	V
		Power-down mode; $V_{CC} = 0 \text{ V}$	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	0	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$T_{amb} = 2$	5 °C					
V_{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$	-	-	$0.35 \times V_{CC}$	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
74AUP2G240		All information provided in this document is subject to legal disclaimers.			© NXP B.V. 2013. All righ	nts reserved.

^[2] For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly with 8.0 mW/K.
For XSON8 and XQFN8 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

Table 7. Static characteristics ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Uni
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = -20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	V _{CC} - 0.1	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_O = -2.7 \text{ mA}$; $V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_O = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
0_		$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.31	V
		$I_{O} = 3.1 \text{ mA; } V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	_	0.31	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	_	0.44	V
ı	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	_	±0.1	μΑ
oz	OFF-state output current	$V_1 = V_{1H}$ or V_{1L} ; $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μА
OFF	power-off leakage current	V_{I} or $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μΑ
∆l _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.2	μΑ
CC	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μΑ
∆l _{CC}	additional supply current	data input; $V_I = V_{CC} - 0.6 \text{ V}$; $I_O = 0 \text{ A}$; $V_{CC} = 3.3 \text{ V}$	<u>[1]</u> -	-	40	μΑ
		$n\overline{OE}$ input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1] -	-	110	μΑ
		disabled inputs; V_I = GND to 3.6 V; $n\overline{OE}$ = V_{CC} ; V_{CC} = 0.8 V to 3.6 V	-	-	1	μА
Cı	input capacitance	$V_{CC} = 0 \text{ V to } 3.6 \text{ V; } V_{I} = \text{GND or } V_{CC}$	-	0.6	-	pF
Co	output capacitance	output enabled; $V_O = GND$; $V_{CC} = 0 V$	-	1.7	-	рF
		output disabled; $V_{CC} = 0 \text{ V}$ to 3.6 V; $V_{O} = \text{GND}$ or V_{CC}	-	1.5	-	рF
T _{amb} = -	40 °C to +85 °C					
√ _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
	-	V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}		-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	_		V

Table 7. Static characteristics ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 \text{ V}$	-	-	$0.30 \times V_{CC}$	V
		V _{CC} = 0.9 V to 1.95 V	-	-	$0.35 \times V_{CC}$	٧
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	0.9	٧
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = -20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	V _{CC} - 0.1	-	-	٧
		$I_O = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7 \times V_{CC}$	-	-	٧
		$I_O = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	٧
		$I_O = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	٧
		$I_O = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	٧
		$I_O = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	٧
		$I_O = -2.7 \text{ mA}$; $V_{CC} = 3.0 \text{ V}$	2.67	-	-	٧
		$I_{O} = -4.0 \text{ mA}$; $V_{CC} = 3.0 \text{ V}$	2.55	-	-	٧
V _{OL}	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$					
02			-	-	0.1	V
			-	-	$0.3 \times V_{CC}$	V
			-	-		V
			-	-	0.35	V
			-	-		V
			-	-		V
			-	-		V
			-	-		V
l _l	input leakage current		-	-		μΑ
l _{oz}	<u> </u>	$V_I = V_{IH}$ or V_{IL} ; $V_O = 0$ V to 3.6 V;	-	-		μA
l _{OFF}	power-off leakage current		-	-	±0.5	μΑ
ΔI_{OFF}	additional power-off	V_1 or $V_0 = 0 \text{ V to } 3.6 \text{ V}$;	-	-	±0.6	μA
Icc	supply current	V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	0.9	μΑ
Δl _{CC}	additional supply current	data input; $V_I = V_{CC} - 0.6 \text{ V}$; $I_O = 0 \text{ A}$; $V_{CC} = 3.3 \text{ V}$	<u>[1]</u> -	-	50	μΑ
		$n\overline{OE}$ input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1] -	-	120	μΑ
			-	-	1	μΑ
Γ _{amb} = -	40 °C to +125 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.75 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	_	-	V

Table 7. Static characteristics ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	$0.25 \times V_{CC}$	٧
		V _{CC} = 0.9 V to 1.95 V	-	-	$0.30 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V_{CC} = 3.0 V to 3.6 V	-	-	0.25 × V _{CC} 0.30 × V _{CC} 0.7 0.9 0.11 0.33 × V _{CC} 0.41 0.39 0.36 0.50 0.50 0.50 ±0.75 ±0.75 ±0.75	V
VoH	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -20 \mu A$; $V_{CC} = 0.8 \text{ V}$ to 3.6 V	V _{CC} - 0.11	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_{O} = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.33 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		$I_{O} = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.39	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	0.36	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
l _l	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	0.25 × V _{CC} V 0.30 × V _{CC} V 0.7 V 0.9 V - V - V - V - V - V - V - V - V - V	μΑ
l _{oz}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.75	μΑ
OFF	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.75	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
Icc	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ
Δl _{CC}	additional supply current	data input; $V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	<u>[1]</u> -	-	75	μΑ
		$\overline{\text{OE}}$ input; $V_{\text{I}} = V_{\text{CC}} - 0.6 \text{ V}$; $I_{\text{O}} = 0 \text{ A}$; $V_{\text{CC}} = 3.3 \text{ V}$	[1] -	-	180	μΑ
		disabled inputs; $V_I = GND$ to 3.6 V; $n\overline{OE} = V_{CC}$; $V_{CC} = 0.8$ V to 3.6 V	-	-	1	μΑ

^[1] One input at V_{CC} – 0.6 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V; for test circuit see Figure 9.

Symbol	Parameter	Conditions		25 °C		-40	0 °C to +1	125 °C	Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
$C_L = 5 pl$									
t _{pd}	propagation delay	nA to nY; see Figure 7							
		$V_{CC} = 0.8 \text{ V}$	-	22.3	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.0	5.8	12.6	2.8	14.1	15.5	ns
		V _{CC} = 1.4 V to 1.6 V	2.3	4.0	7.3	2.1	8.5	9.4	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	3.2	5.5	1.9	6.7	7.4	ns
		V _{CC} = 2.3 V to 2.7 V	1.8	2.6	4.1	1.5	4.8	5.3	ns
		V _{CC} = 3.0 V to 3.6 V	1.4	2.3	3.6	1.3	4.1	4.6	ns
t _{en}	enable time	nOE to nY; see Figure 8							
		V _{CC} = 0.8 V	-	70.2	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.1	6.4	14.3	2.8	15.9	17.5	ns
		V _{CC} = 1.4 V to 1.6 V	2.5	4.4	8.1	2.2	9.5	10.5	ns
		V _{CC} = 1.65 V to 1.95 V	2.1	3.6	6.2	1.9	7.4	8.2	ns
		V _{CC} = 2.3 V to 2.7 V	1.8	2.8	4.6	1.7	5.4	6.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.7	2.5	4.0	1.7	4.7	5.3	ns
t _{dis}	disable time	nOE to nY; see Figure 8							
		$V_{CC} = 0.8 \text{ V}$	-	14.8	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.0	4.3	7.4	2.3	8.3	9.2	ns
		V _{CC} = 1.4 V to 1.6 V	1.6	3.2	5.2	1.7	5.9	6.5	ns
		V _{CC} = 1.65 V to 1.95 V	1.5	3.0	4.8	1.5	5.5	6.1	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.1	2.2	3.5	1.4	4.0	4.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.3	2.5	3.9	1.4	4.5	5.0	ns

Table 8. Dynamic characteristics ...continued Voltages are referenced to GND (ground = 0 V; for test circuit see <u>Figure 9</u>.

Symbol	Parameter	Conditions		25 °C		-40 °C to +125 °C			Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 10 p	o F		'	'	'		'	'	
·pd	propagation delay	nA to nY; see Figure 7	<u>2]</u>						
		V _{CC} = 0.8 V	-	25.7	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.5	6.6	14.5	3.2	16.3	18.0	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	2.2	4.6	8.4	2.0	9.9	10.9	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.0	3.8	6.4	1.8	7.7	8.6	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.8	3.1	4.8	1.7	5.7	6.4	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.7	2.8	4.3	1.7	5.0	5.5	ns
t _{en} enable time	enable time	nOE to nY; see Figure 8	3]						
		V _{CC} = 0.8 V	-	74.0	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.6	7.4	16.3	3.2	18.2	20.1	ns
		V _{CC} = 1.4 V to 1.6 V	2.3	5.1	9.2	2.1	10.9	12.0	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	4.1	7.1	1.8	8.5	9.4	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.8	3.4	5.4	1.7	6.4	7.1	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.8	3.1	4.8	1.7	5.7	6.3	ns
t _{dis}	disable time	nOE to nY; see Figure 8	<u>4]</u>						
		V _{CC} = 0.8 V	-	33.7	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.4	5.4	9.0	3.2	10.0	11.0	ns
		V _{CC} = 1.4 V to 1.6 V	2.1	4.1	6.3	2.1	7.1	7.9	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.3	4.2	6.3	1.8	7.1	7.9	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	3.0	4.6	1.7	5.2	5.7	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.1	3.8	5.7	1.7	6.4	7.1	ns
C _L = 15 p	ρF								
t _{pd}	propagation delay	nA to nY; see Figure 7	2]						
		V _{CC} = 0.8 V	-	29.0	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.9	7.4	16.3	3.6	18.4	20.2	ns
		V _{CC} = 1.4 V to 1.6 V	3.0	5.1	9.4	2.5	11.1	12.3	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.2	4.2	7.2	2.1	8.7	9.6	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	2.0	3.5	5.4	1.9	6.5	7.2	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.0	3.3	4.9	1.9	5.7	6.4	ns
en	enable time	nOE to nY; see Figure 8	3]						
		V _{CC} = 0.8 V	-	77.8	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.0	8.2	18.2	3.6	20.4	22.5	ns
		V _{CC} = 1.4 V to 1.6 V	3.0	5.6	10.3	2.5	12.2	13.4	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.3	4.6	7.9	2.1	9.5	10.5	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	2.1	3.9	6.0	2.0	7.2	7.9	ns
		V _{CC} = 3.0 V to 3.6 V	2.1	3.6	5.5	1.9	6.4	7.1	ns

Low-power dual inverting buffer/line driver; 3-state

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V; for test circuit see Figure 9.

Symbol	Parameter	Conditions			25 °C		-40	–40 °C to +125 °C			
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)		
t _{dis}	disable time	nOE to nY; see Figure 8	<u>[4]</u>				•				
		V _{CC} = 0.8 V		-	62.5	-	-	-	-	ns	
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		4.3	6.6	10.4	3.6	11.6	12.8	ns	
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		3.0	5.0	7.4	2.5	8.4	9.3	ns	
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		3.0	5.3	7.8	2.1	8.7	9.7	ns	
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.1	3.8	5.7	2.0	6.4	7.1	ns	
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.9	5.0	7.4	1.9	8.3	9.1	ns	
C _L = 30 p	oF										
t _{pd}	propagation delay	nA to nY; see Figure 7	[2]								
		V _{CC} = 0.8 V		-	39.1	-	-	-	-	ns	
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		5.0	9.7	21.6	4.6	24.3	26.8	ns	
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		4.0	6.7	12.3	3.0	14.6	16.1	ns	
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.9	5.5	9.5	2.7	11.5	12.6	ns	
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.7	4.6	7.1	2.5	8.6	9.5	ns	
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.6	4.3	6.4	2.5	7.7	8.5	ns	
t _{en}	enable time	nOE to nY; see Figure 8	[3]								
		$V_{CC} = 0.8 \text{ V}$		-	89.4	-	-	-	-	ns	
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		5.2	10.6	23.8	4.6	26.7	29.5	ns	
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		4.0	7.3	13.2	3.0	15.7	17.4	ns	
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		3.0	6.0	10.2	2.7	12.3	13.6	ns	
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.8	5.0	7.8	2.6	9.3	10.3	ns	
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.8	4.8	7.1	2.6	8.4	9.3	ns	
t _{dis}	disable time	nOE to nY; see Figure 8	<u>[4]</u>								
		$V_{CC} = 0.8 \text{ V}$		-	68.9	-	-	-	-	ns	
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		6.0	9.3	15.0	4.6	16.5	18.2	ns	
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		4.4	7.7	11.0	3.0	12.2	13.4	ns	
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		5.1	8.8	12.4	2.7	13.7	15.1	ns	
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		3.6	6.2	9.0	2.6	10.0	11.0	ns	
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		5.2	8.8	12.7	2.6	14.0	15.4	ns	

Dynamic characteristics ...continued Table 8.

Voltages are referenced to GND (ground = 0 V; for test circuit see Figure 9.

Symbol	Parameter	Conditions			25 °C		-4	Unit		
			Mi	n	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
$C_L = 5 pl$	F, 10 pF, 15 pF and	30 pF								
C _{PD} power dissipation		$f = 1 \text{ MHz}$; $V_I = \text{GND to } V_{CC}$	<u>[5]</u>							
	capacitance	$V_{CC} = 0.8 \text{ V}$	-		2.7	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	-		2.9	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	-		3.0	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	-		3.2	-	-	-	-	pF
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-		3.7	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-		4.2	-	-	-	-	pF

- [1] All typical values are measured at nominal V_{CC}.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [3] t_{en} is the same as t_{PZH} and t_{PZL} .
- [4] t_{dis} is the same as t_{PHZ} and t_{PLZ} .
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

 f_i = input frequency in MHz;

 f_0 = output frequency in MHz;

C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$ = sum of the outputs.

12. Waveforms

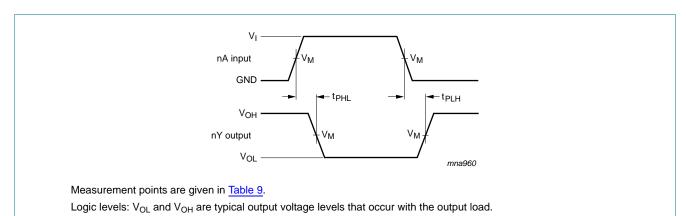


Fig 7. The data input (nA) to output (nY) propagation delays

Table 9. **Measurement points**

Supply voltage	Output	Input		
V _{CC}	V _M	V _M	V _I	$t_r = t_f$
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V_{CC}	≤ 3.0 ns

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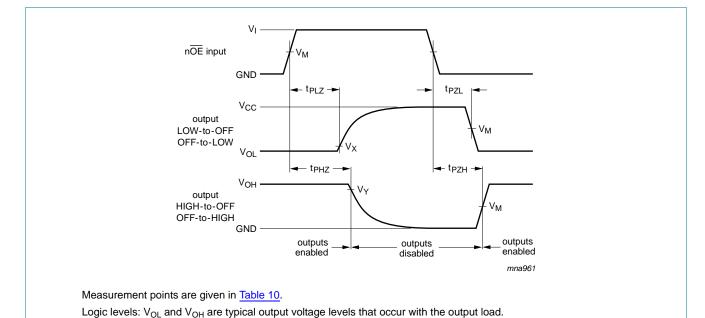
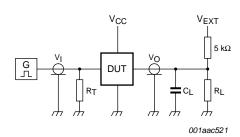


Fig 8. 3-state enable and disable times

Table 10. Measurement points

Supply voltage	Input	Output					
V _{CC}	V _M	V _M	V_X	V _Y			
0.8 V to 1.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{\text{CC}}$	V _{OL} + 0.1 V	$V_{OH} - 0.1 V$			
1.65 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.15 V	V _{OH} – 0.15 V			
3.0 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.3 V	V _{OH} – 0.3 V			



Test data is given in Table 11.

Definitions for test circuit:

R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 9. Test circuit for measuring switching times

Table 11. Test data

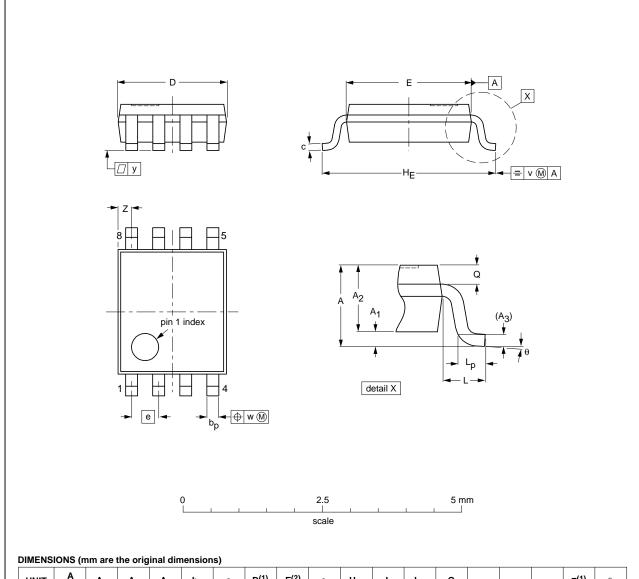
Supply voltage	Load	V _{EXT}				
V _{CC}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}	
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2\times V_{CC}$	

[1] For measuring enable and disable times R_L = 5 $k\Omega$, for measuring propagation delays, setup and hold times and pulse width R_L = 1 $M\Omega$.

13. Package outline

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



UNIT	A max.	A ₁	A ₂	А3	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	q	٧	w	у	Z ⁽¹⁾	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT765-1		MO-187			02-06-07

Fig 10. Package outline SOT765-1 (VSSOP8)

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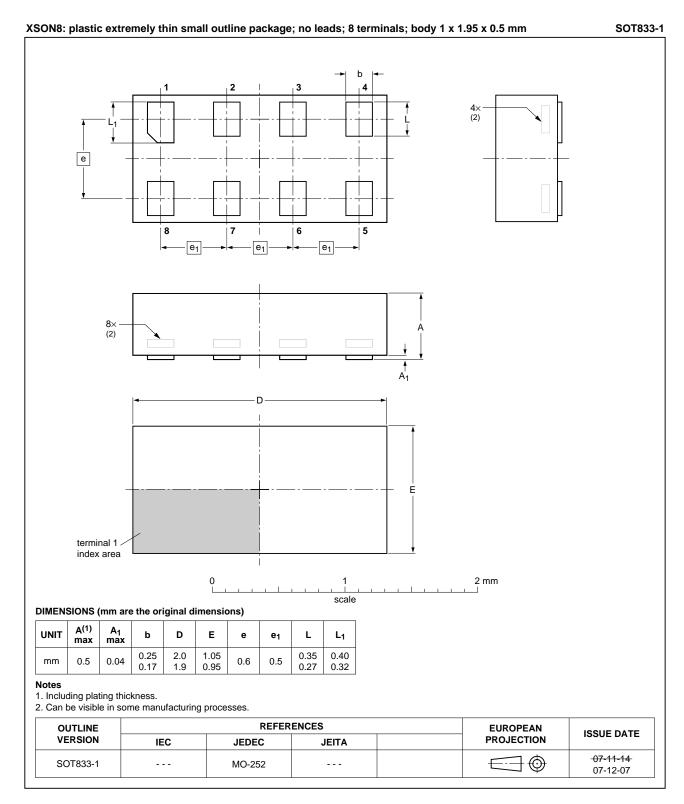


Fig 11. Package outline SOT833-1 (XSON8)

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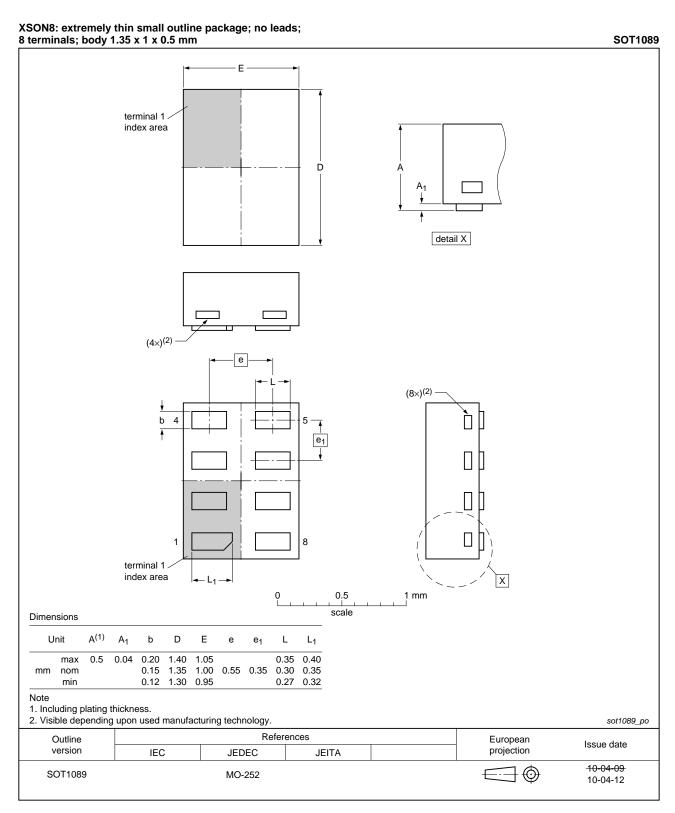


Fig 12. Package outline SOT1089 (XSON8)

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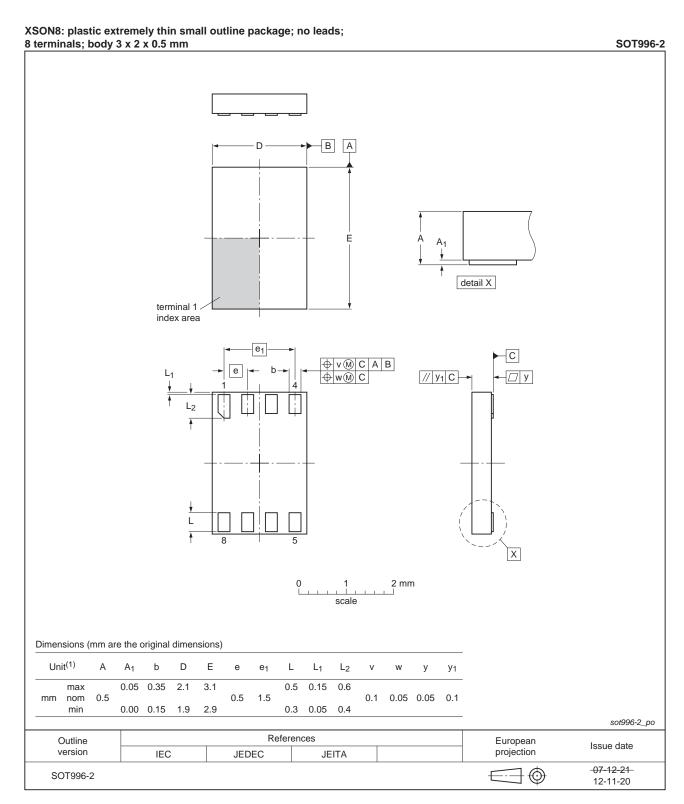


Fig 13. Package outline SOT996-2 (XSON8)

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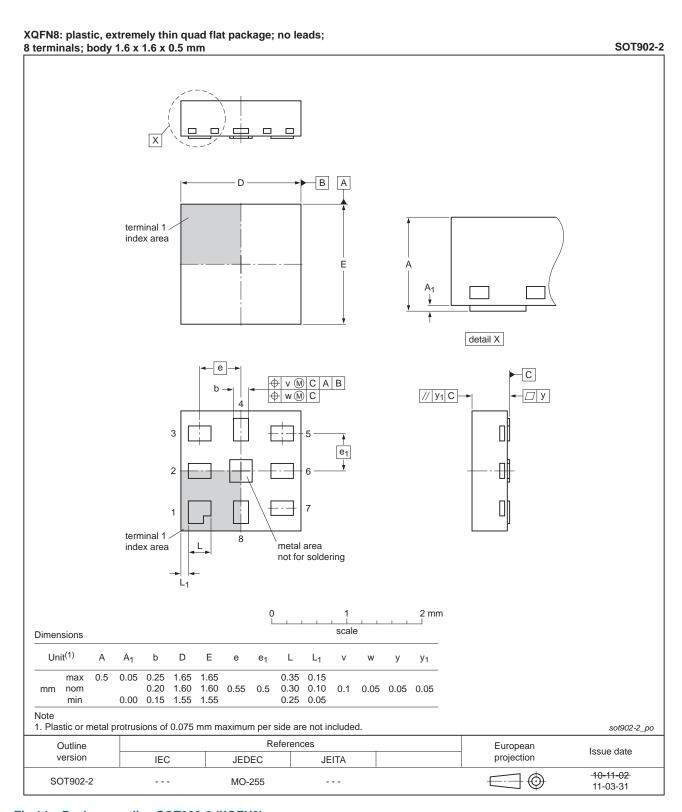


Fig 14. Package outline SOT902-2 (XQFN8)

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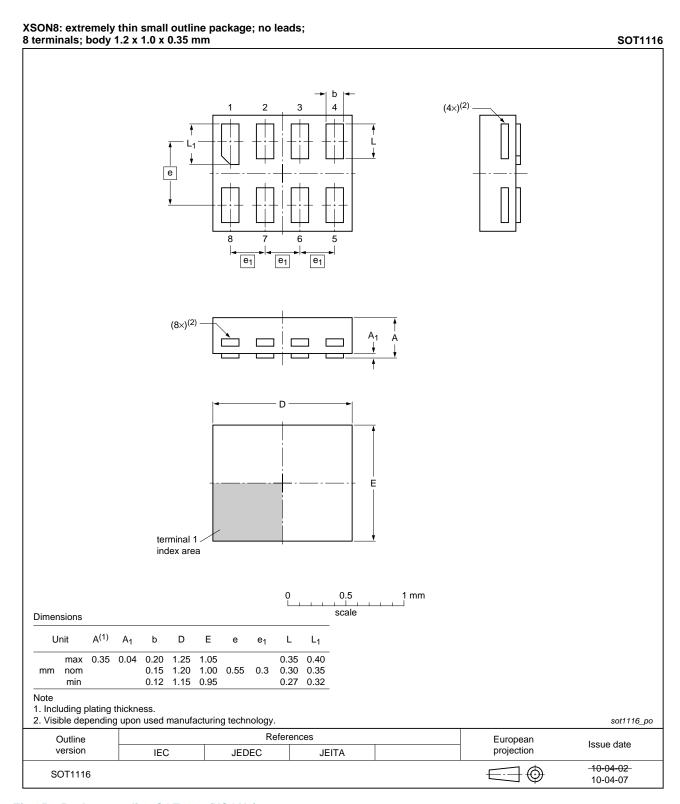


Fig 15. Package outline SOT1116 (XSON8)

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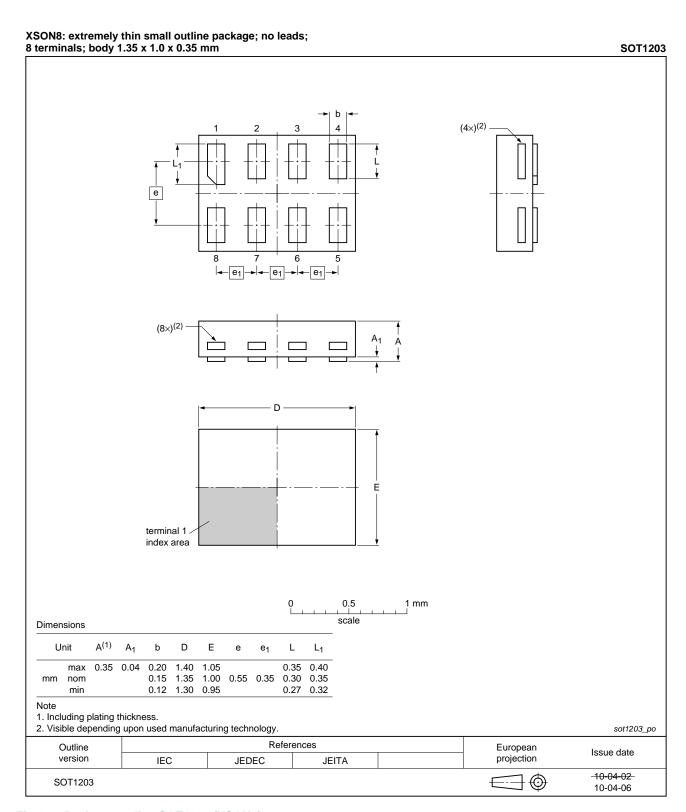


Fig 16. Package outline SOT1203 (XSON8)

14. Abbreviations

Table 12. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

15. Revision history

Table 13. Revision history

74AUP2G240 v.8	20130124			
	_0.001_1	Product data sheet	-	74AUP2G240 v.7
Modifications:	 For type nu 	mber 74AUP2G240GD XS	ON8U has changed to >	(SON8.
74AUP2G240 v.7	20120606	Product data sheet	-	74AUP2G240 v.6
74AUP2G240 v.6	20111205	Product data sheet	-	74AUP2G240 v.5
74AUP2G240 v.5	20100913	Product data sheet	-	74AUP2G240 v.4
74AUP2G240 v.4	20090630	Product data sheet	-	74AUP2G240 v.3
74AUP2G240 v.3	20090407	Product data sheet	-	74AUP2G240 v.2
74AUP2G240 v.2	20080222	Product data sheet	-	74AUP2G240 v.1
74AUP2G240 v.1	20061006	Product data sheet	-	-

16. Legal information

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Document status[1][2]	Product status[3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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